XM1001-BD

Image Reject Mixer
12.0-40.0 GHz

Features
- Fundamental Image Reject Mixer
- 8.0 dB Conversion Loss
- 20.0 dB Image Rejection
- +25.0 dBm Input Third Order Intercept (IIP3)
- 100% On-Wafer RF Testing
- 100% Visual Inspection to MIL-STD-883 Method 2010
- RoHS* Compliant and 260°C Reflow Compatible

Description
M/A-COM Tech’s 12.0-40.0 GHz GaAs MMIC fundamental image reject mixer can be used as an up- or down-converter. The device has a conversion loss of 8.0 dB with a 20.0 dB image rejection across the band. I and Q mixer outputs are provided and an external 90 degree hybrid is required to select the desired sideband. This MMIC uses M/A-COM Tech’s GaAs PHEMT device model technology, and is based upon electron beam lithography to ensure high repeatability and uniformity. The chip has surface passivation to protect and provide a rugged part with backside via holes and gold metallization to allow either a conductive epoxy or eutectic solder die attach process. This device is well suited for Millimeter-wave Point-to-Point Radio, LMDS, SATCOM and VSAT applications.

Ordering Information

<table>
<thead>
<tr>
<th>Part Number</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>XM1001-BD-000V</td>
<td>“V” - vacuum release gel paks</td>
</tr>
<tr>
<td>XM1001-BD-EV1</td>
<td>evaluation module</td>
</tr>
</tbody>
</table>

Absolute Maximum Ratings

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Absolute Max.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Gate Bias Voltage (Vg)</td>
<td>+0.3 VDC</td>
</tr>
<tr>
<td>Input Power (RF Pin)</td>
<td>+20.0 dBm</td>
</tr>
<tr>
<td>Input Power (IF Pin)</td>
<td>+20.0 dBm</td>
</tr>
<tr>
<td>Storage Temperature (Tstg)</td>
<td>-65 °C to +165 °C</td>
</tr>
<tr>
<td>Operating Temperature (Ta)</td>
<td>-55 °C to +125 °C</td>
</tr>
</tbody>
</table>
## Electrical Specifications: 12-40 GHz (Upper Side Band) (Ambient Temperature T = 25°C)

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Units</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Frequency Range (RF) Lower Side Band</td>
<td>GHz</td>
<td>12.0</td>
<td>-</td>
<td>38.0</td>
</tr>
<tr>
<td>Frequency Range (LO)</td>
<td>GHz</td>
<td>8.0</td>
<td>-</td>
<td>42.0</td>
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<tr>
<td>Frequency Range (IF)</td>
<td>GHz</td>
<td>DC</td>
<td>-</td>
<td>4.0</td>
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<tr>
<td>RF Return Loss (S11)</td>
<td>dB</td>
<td>-</td>
<td>10.0</td>
<td>-</td>
</tr>
<tr>
<td>IF Return Loss (S22)</td>
<td>dB</td>
<td>-</td>
<td>TBD</td>
<td>-</td>
</tr>
<tr>
<td>LO Return Loss (S33)</td>
<td>dB</td>
<td>-</td>
<td>TBD</td>
<td>-</td>
</tr>
<tr>
<td>Conversion Loss (S21)</td>
<td>dB</td>
<td>-</td>
<td>8.0</td>
<td>-</td>
</tr>
<tr>
<td>LO Input Drive (P_{LO})</td>
<td>dBm</td>
<td>-</td>
<td>+12.0</td>
<td>-</td>
</tr>
<tr>
<td>Image Rejection</td>
<td>dBc</td>
<td>-</td>
<td>20.0</td>
<td>-</td>
</tr>
<tr>
<td>Isolation LO/RF</td>
<td>dB</td>
<td>-</td>
<td>16.0</td>
<td>-</td>
</tr>
<tr>
<td>Isolation LO/IF</td>
<td>dB</td>
<td>-</td>
<td>TBD</td>
<td>-</td>
</tr>
<tr>
<td>Isolation RF/IF</td>
<td>dB</td>
<td>-</td>
<td>TBD</td>
<td>-</td>
</tr>
<tr>
<td>Input Third Order Intercept (IIP3)</td>
<td>dBm</td>
<td>-</td>
<td>+25.0</td>
<td>-</td>
</tr>
<tr>
<td>Gate Bias Voltage (Vg1)</td>
<td>VDC</td>
<td>-2.0</td>
<td>-0.5</td>
<td>+0.1</td>
</tr>
</tbody>
</table>
XM1001-BD

Image Reject Mixer
12.0-40.0 GHz
Rev. V1

Typical Performance Curves

XM1001-BD Vg=0.5 VDC, USB
LO=12.0 dBm, IF=2.0 GHz, RF=20.0 dBm, ~4840 Devices

XM1001-BD Vg=0.5 VDC, LSB
LO=12.0 dBm, IF=2.0 GHz, RF=20.0 dBm, ~4840 Devices

XM1001-BD Vg=0.5 VDC, USB
LO=12.0 dBm, IF=2.0 GHz, RF=20.0 dBm, ~4840 Devices

XM1001-BD Vg=0.5 VDC, LSB
LO=12.0 dBm, IF=2.0 GHz, RF=20.0 dBm, ~4840 Devices
Typical Performance Curves (cont.)
Typical Performance Curves (cont.)

(Vg=0.5V, PRF=-10dBm IF=2GHz): USB PLO=-12dBm
Image Rejection (dBC) & Conversion Gain (dB) vs. LO freq (GHz) & RF freq (GHz)

(USB, Vg=0.5V, PRF=-10dBm, IF=2GHz): 1 device and different powers
Image Rejection (dBC) & Conversion Gain (dB) vs. LO freq (GHz) & RF freq (GHz)

USB Conversion Gain/Image Rejection vs Frequency and for different Vg bias (-2.1V to 0.1V
with 0.2V steps) PLO=-12dBm

(LSB, Vg=0.5V, PRF=-10dBm, IF=2GHz): 1 device and different powers
Image Rejection (dBC) & Conversion Gain (dB) vs. LO freq (GHz) & RF freq (GHz)

LSB Conversion Gain vs Frequency and for different Vg bias (-2.1V to 0.1V with 0.2V steps)
PLO=-12dBm
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Rev. V1

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Typical Performance Curves (cont.)
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Image Reject Mixer
12.0-40.0 GHz

Typical Performance Curves (cont.)
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12.0-40.0 GHz

Mechanical Drawing

Bias Arrangement

Bypass Capacitors - See App Note [2]
**App Note [1] Biasing** - As shown in the bonding diagram, the pHEMT mixer devices are operated using a separate gate voltage Vg1. Set Vg1=-0.5V for optimum conversion loss performance.

**App Note [2] Bias Arrangement** - Each DC pad (Vg1) needs to have DC bypass capacitance (~100-200 pF) as close to the device as possible. Additional DC bypass capacitance (~0.01 uF) is also recommended.

**App Note [3] USB/LSB Selection** -

For **Upper Side Band Operation (USB)**: With IF1 and IF2 connected to the direct port (0º) and coupled port (90º) respectively as shown in the diagram, the USB signal will reside on the isolated port. The input port must be loaded with 50 ohms.

For **Lower Side Band Operation (LSB)**: With IF1 and IF2 connected to the direct port (0º) and coupled port (90º) respectively as shown in the diagram, the LSB signal will reside on the input port. The isolated port must be loaded with 50 ohms.

**Note**: The coupled port can be used as an alternative input but the port location of the Coupled and Direct ports reverse.

An alternate method of Selection of USB or LSB:

- **USB**
  - In Phase Combiner
  - IF2
  - IF1
  - -90º

- **LSB**
  - In Phase Combiner
  - IF2
  - IF1
  - -90º
Handling Procedures
Please observe the following precautions to avoid damage:

Static Sensitivity
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these class 2 devices.